

TOSHIBA Diode Silicon Epitaxial Planar Type

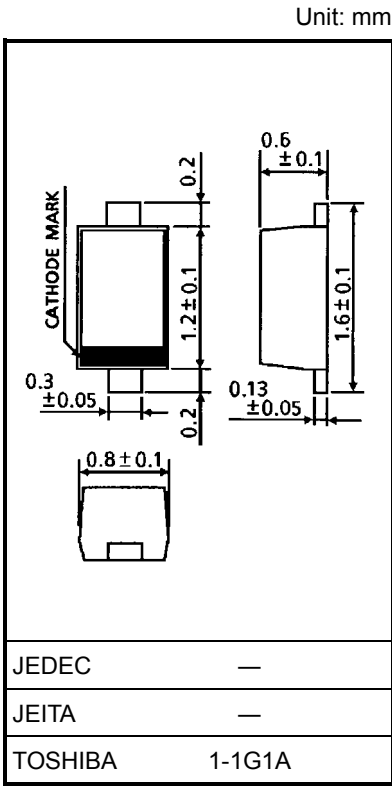
JDV2S14E

Useful for VCO/TCXO

- Small Package
- High Capacitance Ratio: $C_{1V}/C_{2.5V} = 2.15$ (typ.)
- Low Series Resistance : $r_s = 0.4 \Omega$ (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	10	V
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C



Weight: 0.0014 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	$I_R = 1 \mu A$	10	—	—	V
Reverse current	I_R	$V_R = 10 V$	—	—	3	nA
Capacitance	$C_{0.5V}$	$V_R = 0.5 V, f = 1 MHz$	56.3	—	64.7	pF
	C_{1V}	$V_R = 1 V, f = 1 MHz$	44	—	49.5	
	$C_{2.5V}$	$V_R = 2.5 V, f = 1 MHz$	19	—	26.5	
	C_{4V}	$V_R = 4 V, f = 1 MHz$	9.2	—	12	
Capacitance ratio	$C_{0.5V}/C_{1V}$	—	1.25	—	1.35	—
	$C_{1V}/C_{2.5V}$	—	1.99	2.15	2.3	
Series resistance	r_s	$V_R = 4 V, f = 100 MHz$	—	0.4	0.8	Ω

Note: Signal level when capacitance is measured. $V_{sig} = 500 mV_{rms}$

Marking

